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Mr. Cuomo received the B.S. degree in chemistry from Manhattan College in 1958 and the M.S. degree in physical chemistry from St. John's University, Jamaica, New York, in 1960, where he also served as a teaching assistant. He joined the IBM Research Division in 1963 and is presently manager of a materials area at the Thomas J. Watson Research Center. His interests are in processes for materials preparation, which include sputter deposition, chemical vapor deposition, and electrodeposition. Some particular interests are in epitaxy, stoichiometric compound formation, and in the preparation of materials in their metastable states. Mr. Cuomo received an IBM Outstanding Invention Award in 1972 for his work in the area of amorphous magnetic bubble material. He is a senior member of the American Vacuum Society and also a member of Sigma Xi.

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Mrs. Merritt first joined IBM in 1970 at the Thomas J. Watson Research Center, Yorktown Heights, New York, where she worked on the preparation of new materials via photochemical routes and on the study of photochemical mechanisms. In 1974 she transferred to an organic solid state group, where her research included the preparation and study of new organic materials with interesting solid state properties and the development of solid state devices based on these materials. She has authored a book chapter on organic photovoltaic principles. Mrs. Merritt is now an assistant editor of the *IBM Journal of Research and Development*. She studied chemical engineering at Cornell University, Ithaca, New York, from 1962 to 1964, and received the B.S. in chemistry from Columbia University, New York, in 1967, and the M.S. in organic photochemistry from New York University in 1969. Mrs. Merritt is a member of the American Chemical Society.

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Mr. Pettit is in a semiconductor science and technology department at the Thomas J. Watson Research Center. He is currently involved with research on the optical properties of solar energy materials. He joined IBM in 1956 at the research laboratory in

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Mr. Woodall manages an electro-optical semiconductor devices group at the Thomas J. Watson Research Center. His work has included fabrication of GaAs/Si infrared emitting diodes, as well as research on high efficiency GaAlAs-GaAs solar cells and on photothermal conversion devices. He has received three IBM Outstanding Contribution Awards in 1969, 1970, and 1972 for his work in related areas. Mr. Woodall received his B.S. in metallurgy from the Massachusetts Institute of Technology in 1960, and joined the Research Division in 1962. Prior to this, he was associated with the Clevite Corporation. He is a member of the American Physical Society and the Electrochemical Society.

Kuei H. Yang

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Dr. Yang joined IBM in 1967 and until 1972 worked on chemomechanical techniques for polishing silicon wafers. He has since been using transmission and scanning electron microscopy, as well as x-ray topography, for the characterization of materials and the investigation of defects. He earned his degrees in chemical engineering: the B.S. from Tunghai University, Taiwan, in 1963, the M.S. from the University of Missouri, Rolla, in 1967, and the Ph.D. from Washington University, St. Louis, Missouri, in 1972. Dr. Yang is a member of the Electrochemical Society.

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